

TENTATIVE

Features and Applications

- Low ON-state resistance.
- 4V drive.

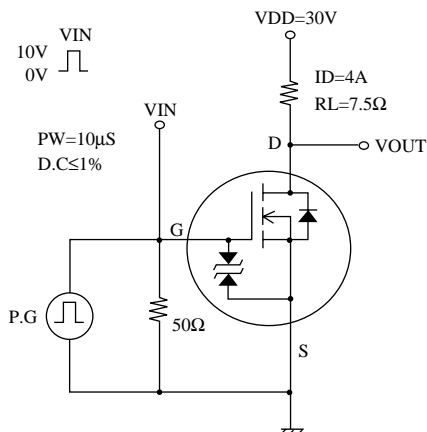
Absolute Maximum Ratings / Ta=25°C

			unit
Drain to Source Voltage	VDSS	60	V
Gate to Source Voltage	VGSS	±20	V
Drain Current (DC)	ID	8	A
Drain Current (Pulse)	IDP	PW≤10μS, dutycycle≤1%	32
Allowable power Dissipation	PD		1
		Tc=25°C	15
Channel Temperature	Tch	150	°C
Storage Temperature	Tstg	-55 to +150	°C

Electrical Characteristics / Ta=25°C

			min	typ	max	unit
Drain to Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0	60			V
Zero Gate Voltage Drain Current	IDSS	VDS=60V, VGS=0			10	μA
Gate to Source Leakage Current	IGSS	VGS=±16V, VDS=0			±10	μA
Cutoff Voltage	VGS(off)	VDS=10V, ID=1mA	1.0		2.4	V
Forward Transfer Admittance	yfs	VDS=10V, ID=4A	3.8	5.5		S
Static Drain to Source on State Resistance	RDS(on)1	ID=4A, VGS=10V		115	150	mΩ
	RDS(on)2	ID=4A, VGS=4V		150	210	mΩ
Input Capacitance	Ciss	VDS=20V, f=1MHz		220		pF
Output Capacitance	Coss	VDS=20V, f=1MHz		75		pF
Reverse Transfer Capacitance	Crss	VDS=20V, f=1MHz		25		pF
Turn-ON Delay Time	td(on)	See Specified Test Circuit .		6		ns
Rise Time	tr			15		ns
Turn-off Delay Time	td(off)			25		ns
Fall Time	tf			15		ns
Total Gate Charge	Qg	VDS=10V, VGS=10V, ID=8A		8		nC
Gate Source Charge	Qgs			1.5		nC
Gate Drain Charge	Qgd			2		nC
Diode Forward Voltage	VSD	IS = 8A, VGS = 0	0.95		1.2	V

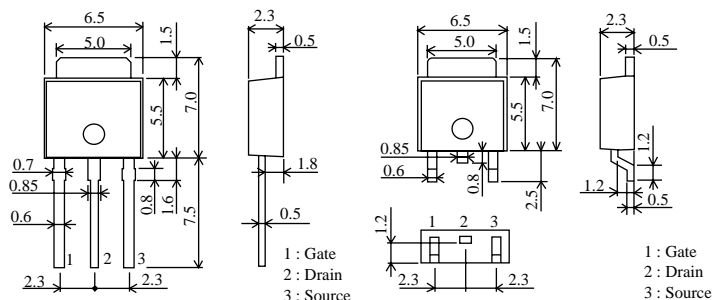
Switching Time Test Circuit



Case Outline

TP(unit:mm)

TP-FA(unit : mm)



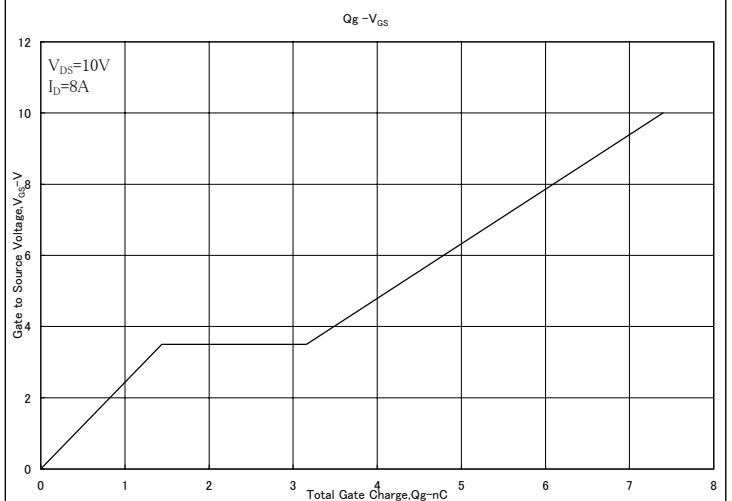
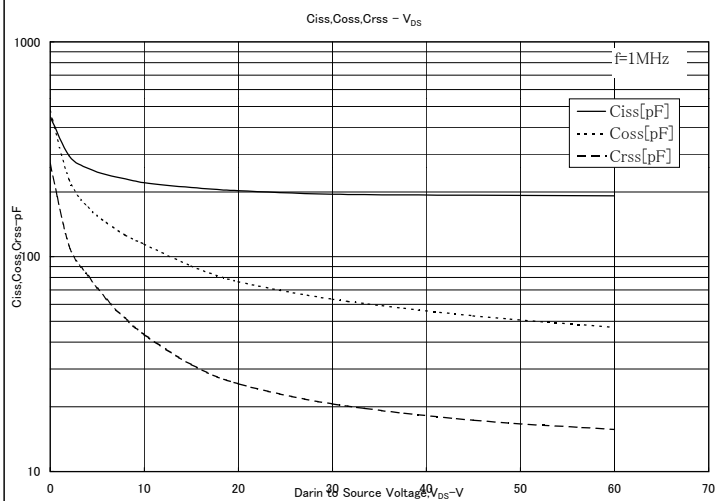
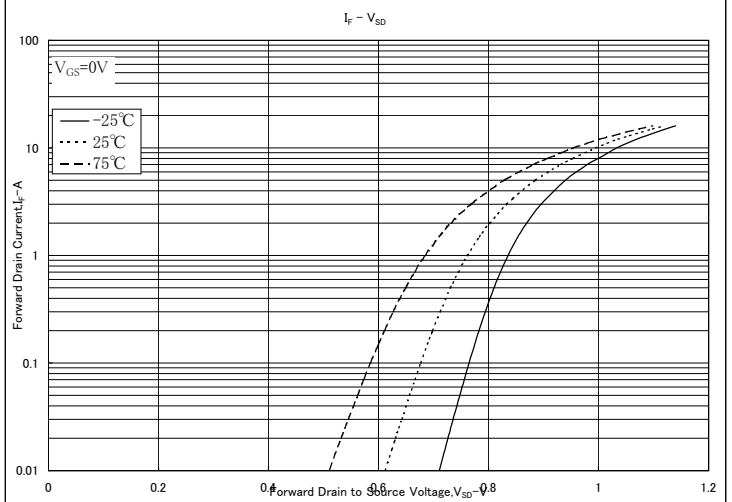
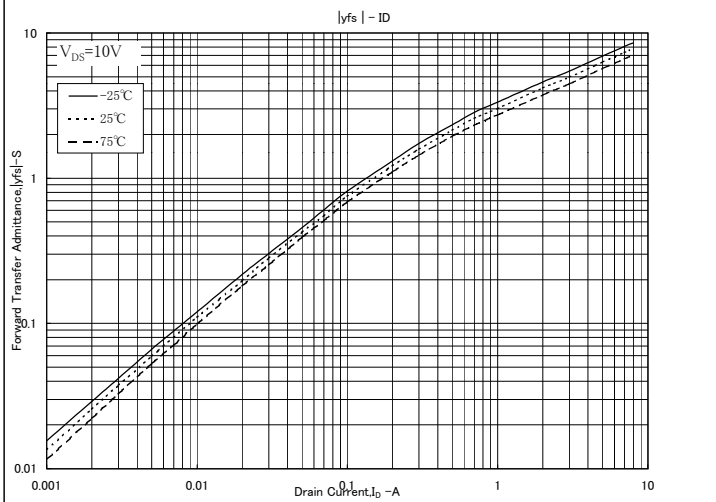
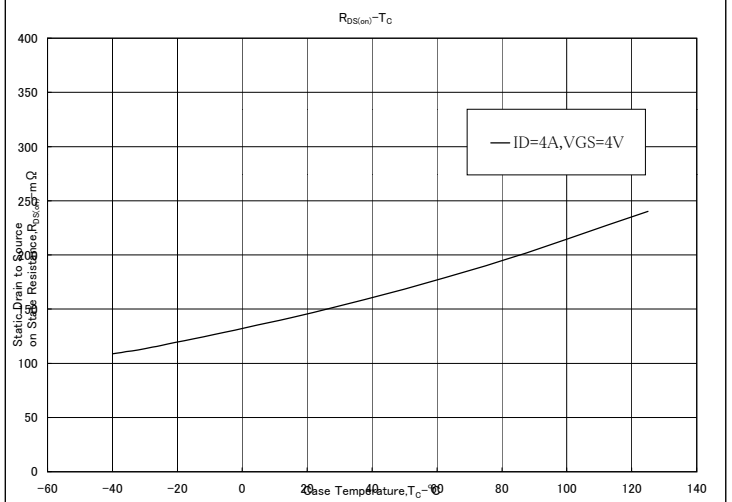
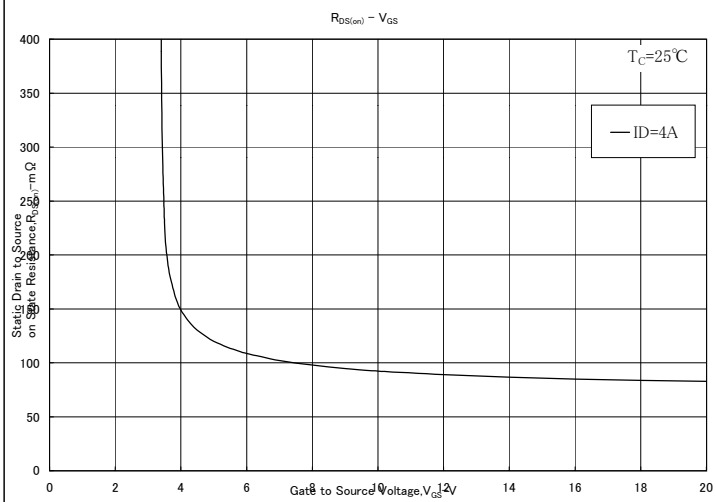
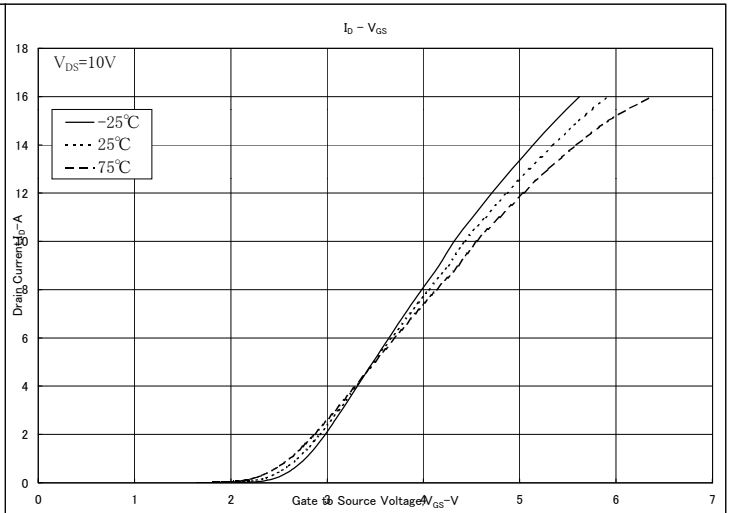
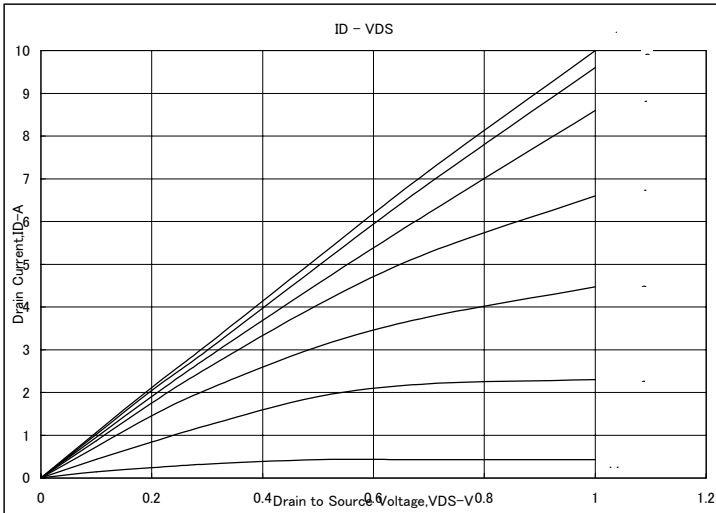
Specifications and information herein are subject to change without notice.

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TM3055カタログ



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